200V N-Channel MOSFETs

PDH50N20

General Description

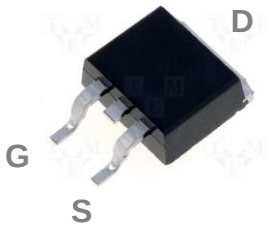
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

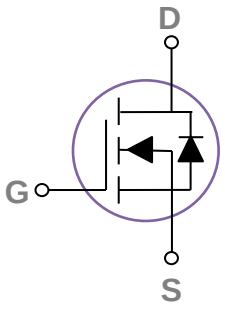
BVDSS	RDSON	ID
200V	24mΩ	60A

Features

- *200V,60A, RDS(ON) =24mΩ@VGS = 10V*
- *Improved dv/dt capability*
- *Fast switching*
- *100% EAS Guaranteed*
- *Green Device Available*

TO263 Pin Configuration





Applications

- *Networking*
- *Load Switch*
- *LED applications*
- *Quick Charger*

Absolute Maximum Ratings Tc=25℃ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	200	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current – Continuous (T_C=25℃) (Chip Limitation)	60	A
	Drain Current – Continuous (T_C=100℃) (Chip Limitation)	38	A
I_{DM}	Drain Current – Pulsed[1]	240	A
EAS	Single Pulse Avalanche Energy[2]	280	mJ
IAS	Single Pulse Avalanche Current[2]	75	A
P_D	Power Dissipation (T_C=25℃)	208	W
	Power Dissipation – Derate above 25℃	1.66	W/℃
T_{STG}	Storage Temperature Range	-50 to 150	℃
T_J	Operating Junction Temperature Range	-50 to 150	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	℃/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	0.6	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	200	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.23	---	V/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=200V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=160V , V_{GS}=0V , T_J=125℃	---	---	10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=12A	---	19	24	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.5	2.2	3	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4	---	mV/℃
gfs	Forward Transconductance	V_{DS}=5V , I_D=10A	---	35	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge[3,4]	V_{DS}=160V , V_{GS}=10V , I_D=10A	---	238	450	nC
Q_{gs}	Gate-Source Charge[3,4]		---	62	140	
Q_{gd}	Gate-Drain Charge[3,4]		---	58	150	
$T_{d(on)}$	Turn-On Delay Time[3,4]	V_{DD}=50V , V_{GS}=10V , R_G=6Ω I_D=1A	---	55.2	100	ns
T_r	Rise Time[3,4]		---	64.6	120	
$T_{d(off)}$	Turn-Off Delay Time[3,4]		---	202	400	
T_f	Fall Time[3,4]		---	88	160	
C_{iss}	Input Capacitance	V_{DS}=25V , V_{GS}=0V , F=1MHz	---	15325	22000	pF
C_{oss}	Output Capacitance		---	573	900	
C_{rss}	Reverse Transfer Capacitance		---	34	70	
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, F=1MHz	---	1.8	3.6	Ω

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	60	A
I_{SM}	Pulsed Source Current		---	---	120	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1	V

Note :
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=50V,V_{GS}=10V,L=0.1mH,I_{AS}=75A.,R_G=25Ω,Starting T_J=25℃.
3. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
4. Essentially independent of operating temperature.

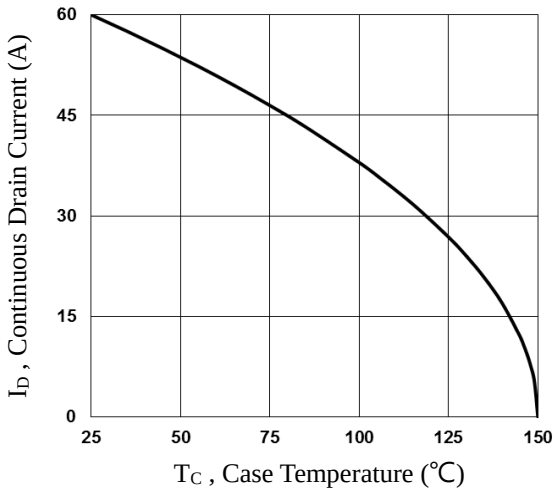


Fig.1 Continuous Drain Current vs. T_C

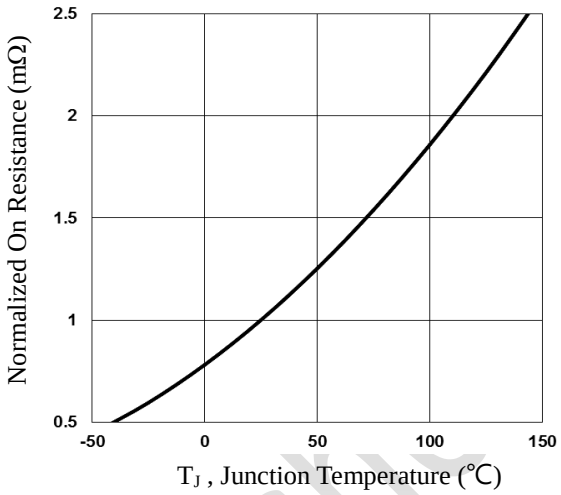


Fig.2 Normalized RDSON vs. T_J

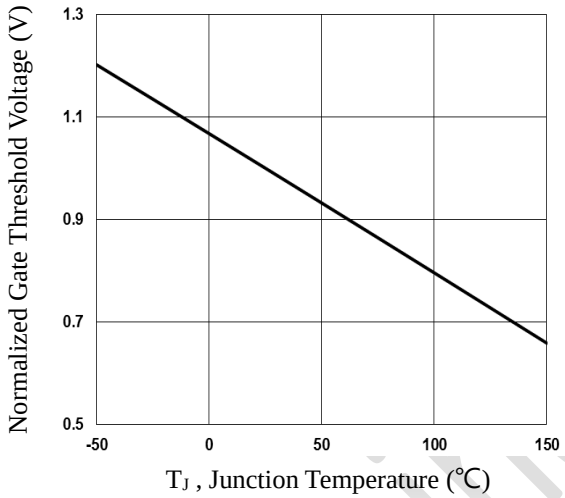


Fig.3 Normalized Vth vs. T_J

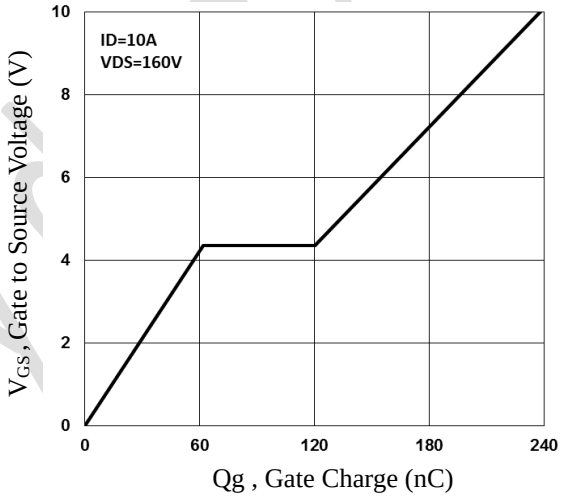


Fig.4 Gate Charge Characteristics

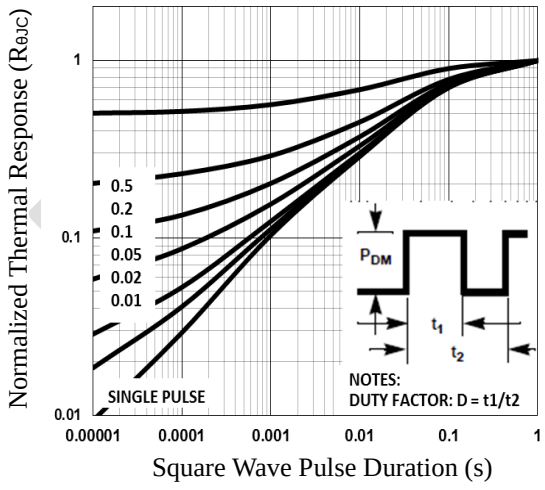


Fig.5 Normalized Transient Impedance

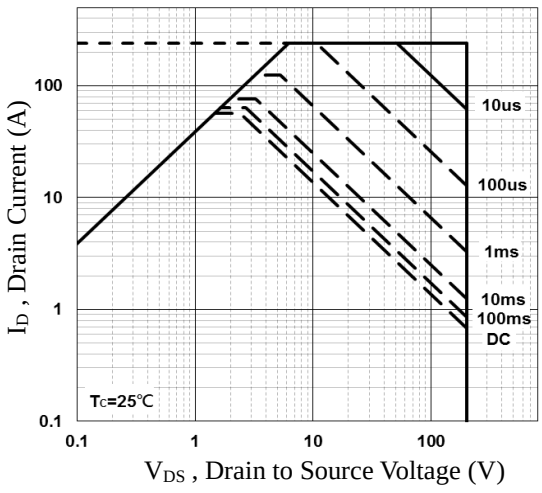


Fig.6 Maximum Safe Operation Area

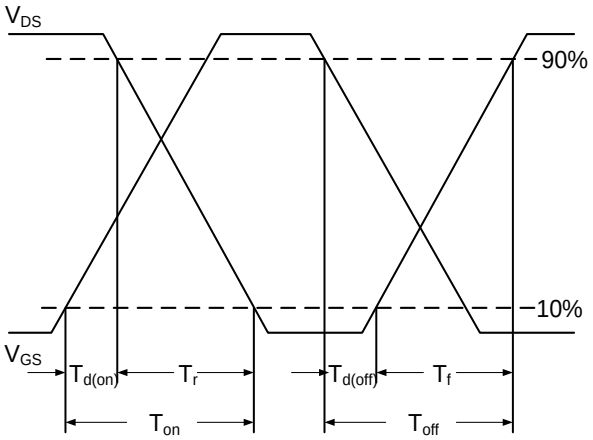


Fig.7 Switching Time Waveform

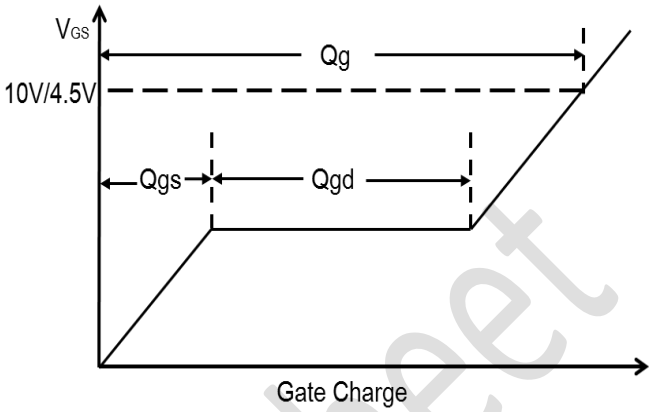


Fig.8 Gate Charge Waveform

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